



**STF42**

## SMALL SIGNAL NPN TRANSISTOR

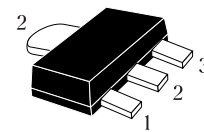
PRELIMINARY DATA

Type	Marking
STF42	642

- SILICON EPITAXIAL PLANAR NPN HIGH VOLTAGE TRANSISTOR
- MINIATURE SOT-89 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE PNP COMPLEMENTARY TYPE IS STF92

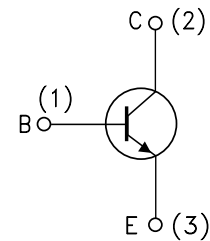
### APPLICATIONS

- VIDEO AMPLIFIER CIRCUITS (RGB CATHODE CURRENT CONTROL)
- TELEPHONE WIRELINE INTERFACE (HOOK SWITCHES, DIALER CIRCUITS)



**SOT-89**

### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )	300	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	300	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	5	V
$I_C$	Collector Current	0.1	A
$I_{CM}$	Collector Peak Current	0.2	A
$P_{tot}$	Total Dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	1.3	W
$T_{stg}$	Storage Temperature	-65 to 150	$^{\circ}\text{C}$
$T_j$	Max. Operating Junction Temperature	150	$^{\circ}\text{C}$

## STF42

### THERMAL DATA

$R_{thj-amb}$	• Thermal Resistance Junction-Ambient	Max	96.1	°C/W
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• Device mounted on a PCB area of 1 cm<sup>2</sup>

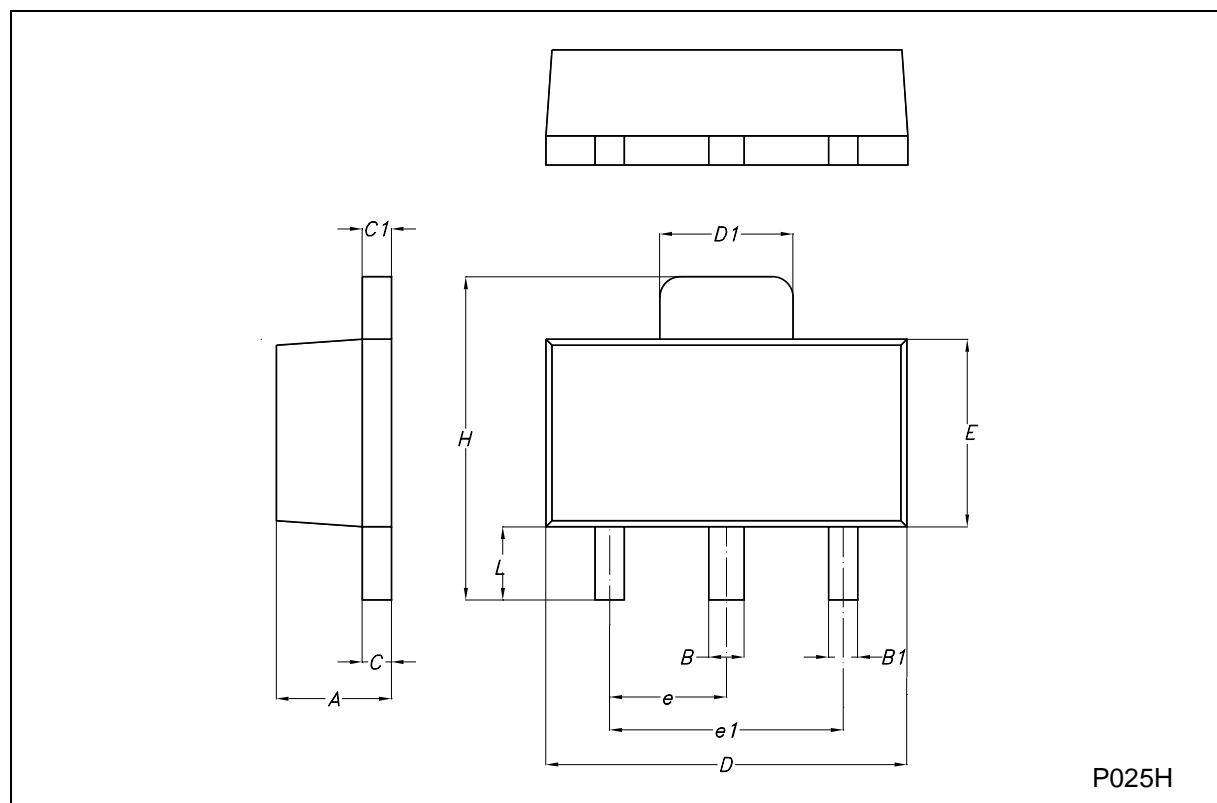
### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CBO}$	Collector Cut-off Current ( $I_E = 0$ )	$V_{CB} = 200\text{ V}$ $V_{CB} = 200\text{ V}$ $T_C = 150\text{ °C}$ $V_{CB} = 300\text{ V}$			10 10 100	nA μA μA
$I_{EBO}$	Emitter Cut-off Current ( $I_C = 0$ )	$V_{EB} = 5\text{ V}$			50	nA
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ( $I_E = 0$ )	$I_C = 100\text{ μA}$	300			V
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage ( $I_B = 0$ )	$I_C = 10\text{ mA}$	300			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ( $I_C = 0$ )	$I_E = 100\text{ μA}$	5			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 30\text{ mA}$ $I_B = 5\text{ mA}$			0.6	V
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = 30\text{ mA}$ $I_B = 5\text{ mA}$			1.2	V
$h_{FE}^*$	DC Current Gain	$I_C = 30\text{ mA}$ $V_{CE} = 10\text{ V}$	75			
$f_T$	Transition Frequency	$I_C = 15\text{ mA}$ $V_{CE} = 10\text{ V}$ $f = 20\text{ MHz}$	60			MHz
$C_{CBO}$	Collector-Base Capacitance	$I_E = 0$ $V_{CB} = 10\text{ V}$ $f = 1\text{ MHz}$		6		pF
$C_{EBO}$	Emitter-Base Capacitance	$I_C = 0$ $V_{EB} = 2\text{ V}$ $f = 1\text{ MHz}$		22		pF

\* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 1.5 %

# SOT-89 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	1.4		1.6	55.1		63.0
B	0.44		0.56	17.3		22.0
B1	0.36		0.48	14.2		18.9
C	0.35		0.44	13.8		17.3
C1	0.35		0.44	13.8		17.3
D	4.4		4.6	173.2		181.1
D1	1.62		1.83	63.8		72.0
E	2.29		2.6	90.2		102.4
e	1.42		1.57	55.9		61.8
e1	2.92		3.07	115.0		120.9
H	3.94		4.25	155.1		167.3
L	0.89		1.2	35.0		47.2



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